

# UG4A THRU UG4D

**ULTRAFAST EFFICIENT  
PLASTIC RECTIFIER**

**Reverse Voltage  
50 to 200 V  
Forward Current 4 A**

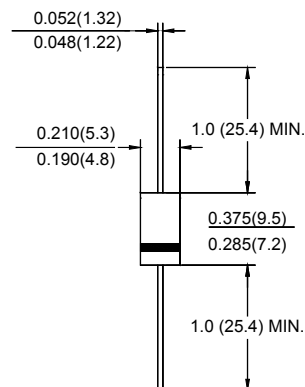
## Features

- Ultrafast recovery time for high efficiency
- Soft recovery characteristics
- Excellent high temperature switching
- Glass passivated junction

## Mechanical Data

- Case: Molded plastic, DO-201AD
- Terminals: Plated axial leads, solderable per MIL-STD-750, method 2026
- Polarity: Color band denotes cathode end
- Mounting position: Any

## DO-201AD



Dimensions in inches and (millimeters)

## Absolute Maximum Ratings and Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbols	UG4A	UG4B	UG4C	UG4D	Units
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	50	100	150	200	V
Maximum RMS Voltage	$V_{RMS}$	35	70	105	140	V
Maximum DC Blocking Voltage	$V_{DC}$	50	100	150	200	V
Maximum Average Forward Rectified Current 0.375"(9.5 mm) Lead Length at $T_L = 75^\circ\text{C}$	$I_{(AV)}$	4				A
Peak Forward Surge Current, 8.3 ms Single Half-sine-wave Superimposed on rated load (JEDEC method) at $T_L = 75^\circ\text{C}$	$I_{FSM}$	150				A
Maximum Forward Voltage at 4 A	$V_F$	0.95				V
Maximum Reverse Current $T_A = 25^\circ\text{C}$ at Rated DC Blocking Voltage $T_A = 100^\circ\text{C}$	$I_R$	5 300				$\mu\text{A}$
Maximum Reverse Recovery Time <sup>1)</sup>	$t_{rr}$	20				ns
Maximum Reverse Recovery Time <sup>2)</sup>	$t_{rr}$	$T_J = 25^\circ\text{C}$ 30 $T_J = 100^\circ\text{C}$ 50				ns
Maximum Recovered stored charge Time <sup>2)</sup>	$Q_{rr}$	$T_J = 25^\circ\text{C}$ 15 $T_J = 100^\circ\text{C}$ 30				nC
Typical Junction Capacitance <sup>3)</sup>	$C_J$	20				pF
Typical Thermal Resistance <sup>4)</sup>	$R_{\theta JA}$	25				$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150				$^\circ\text{C}$

<sup>1)</sup> Reverse recovery test conditions:  $I_F = 0.5\text{ A}$ ,  $I_R = 1\text{ A}$ ,  $I_{rr} = 0.25\text{ A}$ .

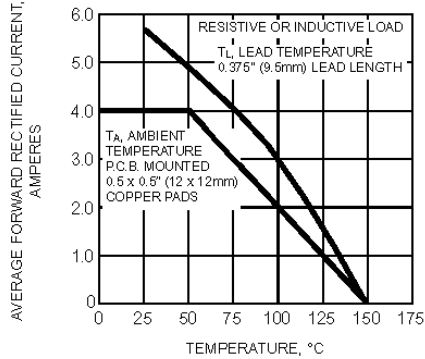
<sup>2)</sup>  $t_{rr}$  and  $Q_{rr}$  measured at tester:  $I_F = 4\text{ A}$ ,  $V_R = 30\text{ V}$ ,  $di/dt = 50\text{ A}/\mu\text{s}$ ,  $I_{rr} = 10\% I_{RM}$  for measurement of  $t_{rr}$ .

<sup>3)</sup> Measured at 1 MHz and applied reverse voltage of 4 V.

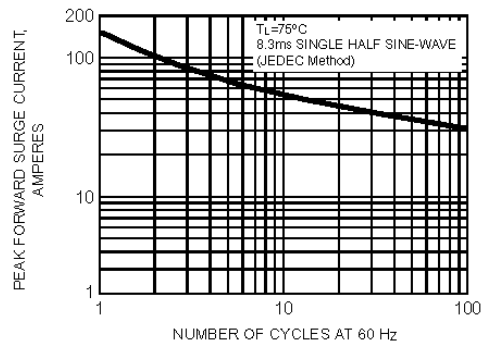
<sup>4)</sup> Thermal resistance from junction to ambient at 0.375" (9.5 mm) lead length.

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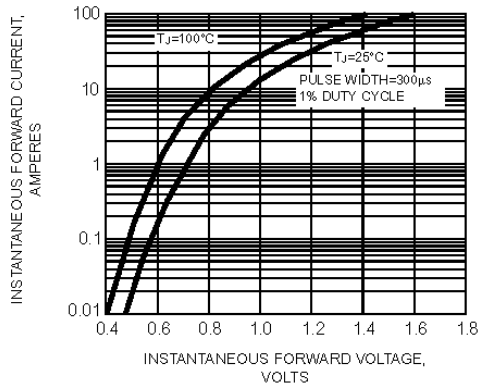
**FIG. 1 - FORWARD CURRENT DERATING CURVE**



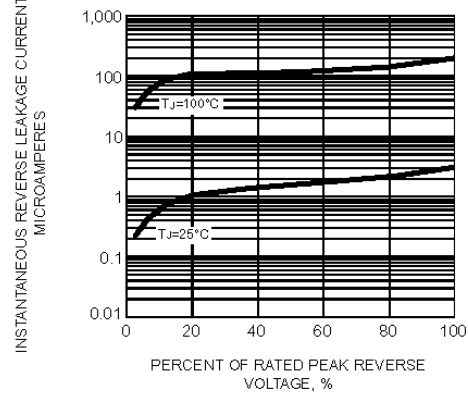
**FIG. 2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT**



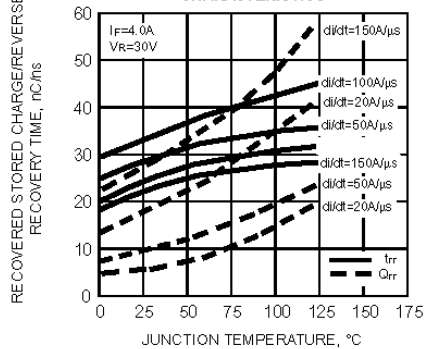
**FIG. 3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS**



**FIG. 4 - TYPICAL REVERSE LEAKAGE CHARACTERISTICS**



**FIG. 5 - REVERSE SWITCHING CHARACTERISTICS**



**FIG. 6 - TYPICAL JUNCTION CAPACITANCE**

